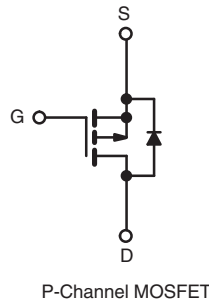
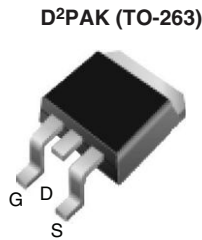


Power MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	- 200	
$R_{DS(on)}$ (Ω)	$V_{GS} = - 10$ V	0.80
Q_g (Max.) (nC)	29	
Q_{gs} (nC)	5.4	
Q_{gd} (nC)	15	
Configuration	Single	



FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- Surface Mount
- Available in Tape and Reel
- Dynamic dV/dt Rating
- Repetitive Avalanche Rated
- P-Channel
- Fast Switching
- Ease of Paralleling
- Compliant to RoHS Directive 2002/95/EC



RoHS*
COMPLIANT
HALOGEN
FREE
Available

DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The D²PAK (TO263) is a surface mount power package capable of accommodating die size up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface mount package. The D²PAK (TO263) is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2.0 W in a typical surface mount application.

ORDERING INFORMATION		
Package	D ² PAK (TO263)	D ² PAK (TO263)
Lead (Pb)-free and Halogen-free	SiHF9630S-GE3	SiHF9630STRL-GE3 ^a
Lead (Pb)-free	IRF9630SPbF	IRF9630STRLPbF ^a
	SiHF9630S-E3	SiHF9630STL-E3 ^a

Note

a. See device orientation.

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V_{DS}	- 200	V	
Gate-Source Voltage		V_{GS}	± 20		
Continuous Drain Current	V_{GS} at - 10 V	I_D	$T_C = 25$ °C	- 6.5	A
			$T_C = 100$ °C	- 4.0	
Pulsed Drain Current ^a		I_{DM}	- 26	W/°C	
Linear Derating Factor			0.59		
Linear Derating Factor (PCB Mount) ^e			0.025		
Single Pulse Avalanche Energy ^b		E_{AS}	500	mJ	
Avalanche Current ^a		I_{AR}	- 6.4	A	
Repetitive Avalanche Energy ^a		E_{AR}	7.4	mJ	
Maximum Power Dissipation	$T_C = 25$ °C	P_D	74	W	
			$T_A = 25$ °C		3.0
Maximum Power Dissipation (PCB Mount) ^e			3.0		
Peak Diode Recovery dV/dt ^c		dV/dt	- 5.0	V/ns	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to + 150	°C	
Soldering Recommendations (Peak Temperature)	for 10 s		300 ^d		

Notes

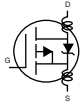

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- $V_{DD} = - 50$ V, starting $T_J = 25$ °C, $L = 17$ mH, $R_g = 25$ Ω , $I_{AS} = - 6.5$ A (see fig. 12).
- $I_{SD} \leq - 6.5$ A, $dI/dt \leq 120$ A/ μ s, $V_{DD} \leq V_{DS}$, $T_J \leq 150$ °C.
- 1.6 mm from case.
- When mounted on 1" square PCB (FR-4 or G-10 material).

* Pb containing terminations are not RoHS compliant, exemptions may apply

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	62	°C/W
Maximum Junction-to-Ambient (PCB Mount) ^a	R_{thJA}	-	40	
Maximum Junction-to-Case (Drain)	R_{thJC}	-	1.7	

Note

a. When mounted on 1" square PCB (FR-4 or G-10 material).

SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX. UNIT	
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$		-200	-	- V	
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$, $I_D = -1\text{ mA}$		-	-0.24	- $V/^\circ\text{C}$	
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$		-2.0	-	-4.0 V	
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20\text{ V}$		-	-	$\pm 100\text{ nA}$	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -200\text{ V}, V_{GS} = 0\text{ V}$		-	-	-100 μA	
		$V_{DS} = -160\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$		-	-	-500 μA	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = -10\text{ V}$	$I_D = -3.9\text{ A}^b$	-	-	0.80 Ω	
Forward Transconductance	g_{fs}	$V_{DS} = -50\text{ V}, I_D = -3.9\text{ A}^b$		2.8	-	- S	
Dynamic							
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = -25\text{ V}, f = 1.0\text{ MHz}$, see fig. 5		-	700	-	
Output Capacitance	C_{oss}			-	200	-	pF
Reverse Transfer Capacitance	C_{rss}			-	40	-	
Total Gate Charge	Q_g	$V_{GS} = -10\text{ V}$	$I_D = -6.5\text{ A}, V_{DS} = -160\text{ V}$, see fig. 6 and 13 ^b	-	-	29	
Gate-Source Charge	Q_{gs}			-	-	5.4	nC
Gate-Drain Charge	Q_{gd}			-	-	15	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -100\text{ V}, I_D = -6.5\text{ A}, R_g = 12\text{ }\Omega, R_D = 15\text{ }\Omega$, see fig. 10 ^b		-	12	-	
Rise Time	t_r			-	27	-	ns
Turn-Off Delay Time	$t_{d(off)}$			-	28	-	
Fall Time	t_f			-	24	-	
Internal Drain Inductance	L_D	Between lead, 6 mm (0.25") from package and center of die contact 		-	4.5	-	
Internal Source Inductance	L_S			-	7.5	-	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p-n junction diode 		-	-	-6.5	
Pulsed Diode Forward Current ^a	I_{SM}			-	-	-26	
Body Diode Voltage	V_{SD}	$T_J = 25\text{ }^\circ\text{C}, I_S = -6.5\text{ A}, V_{GS} = 0\text{ V}^b$		-	-	-6.5 V	
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}, I_F = -6.5\text{ A}, di/dt = 100\text{ A}/\mu\text{s}^b$		-	200	300 ns	
Body Diode Reverse Recovery Charge	Q_{rr}			-	1.9	2.9 μC	
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)					

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

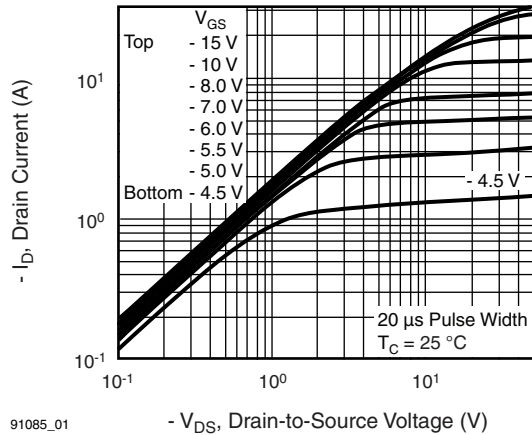


Fig. 1 - Typical Output Characteristics, $T_C = 25\text{ }^\circ\text{C}$

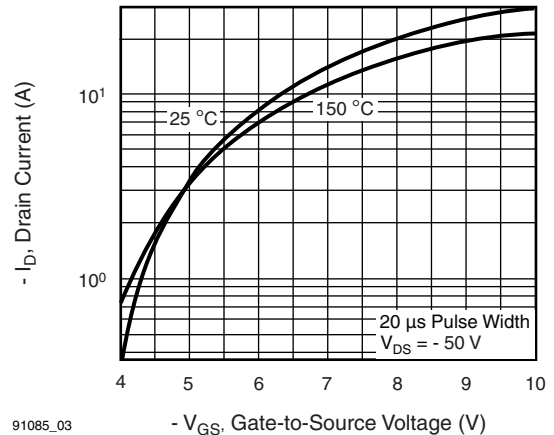


Fig. 3 - Typical Transfer Characteristics

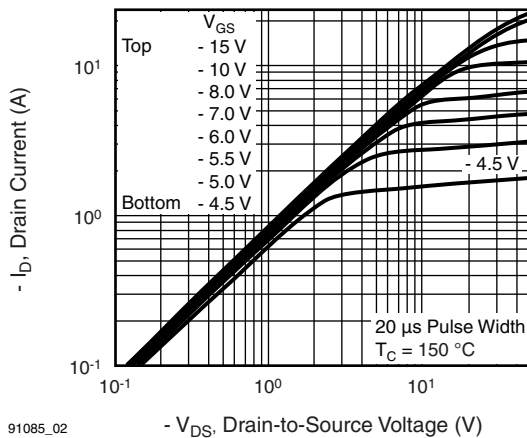


Fig. 2 - Typical Output Characteristics, $T_C = 150\text{ }^\circ\text{C}$

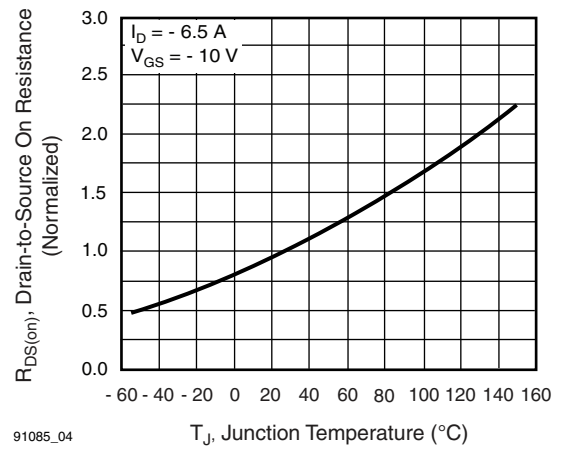
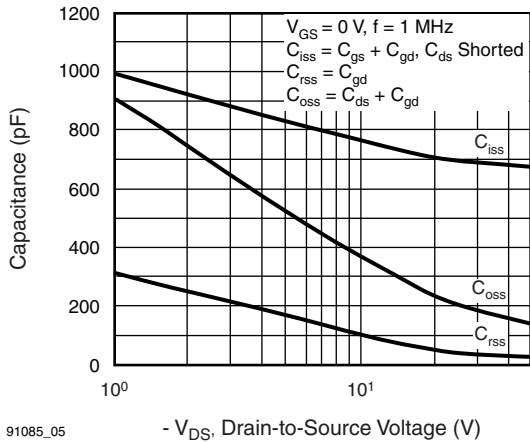
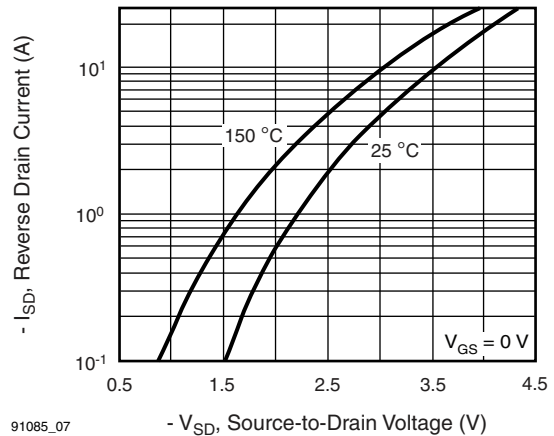


Fig. 4 - Normalized On-Resistance vs. Temperature



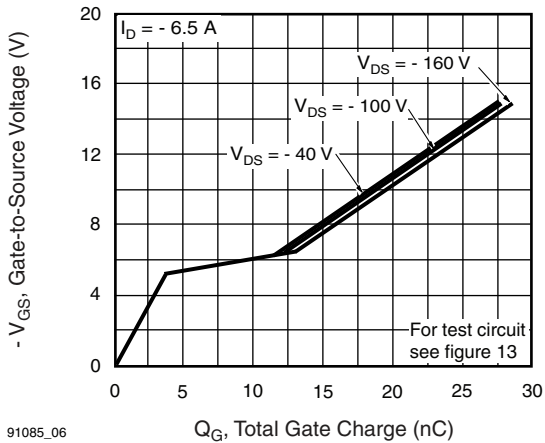
91085_05

Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage



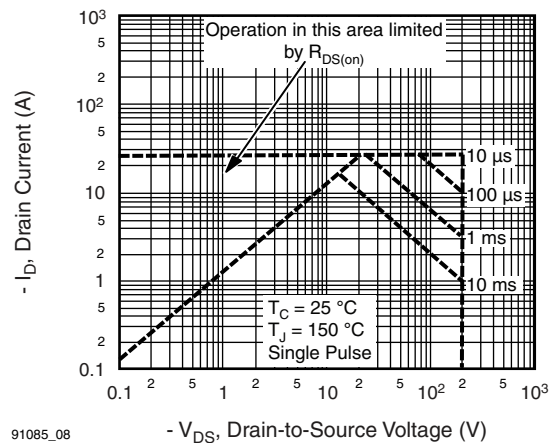
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Fig. 7 - Typical Source-Drain Diode Forward Voltage



91085_06

Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage



91085_08

Fig. 8 - Maximum Safe Operating Area

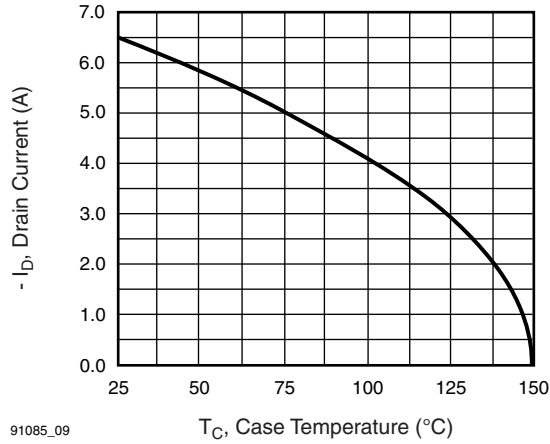


Fig. 9 - Maximum Drain Current vs. Case Temperature

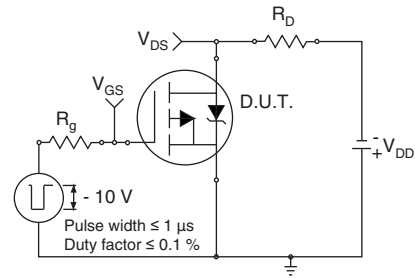


Fig. 10a - Switching Time Test Circuit

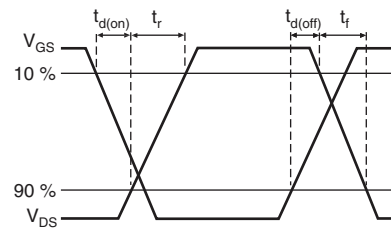


Fig. 10b - Switching Time Waveforms

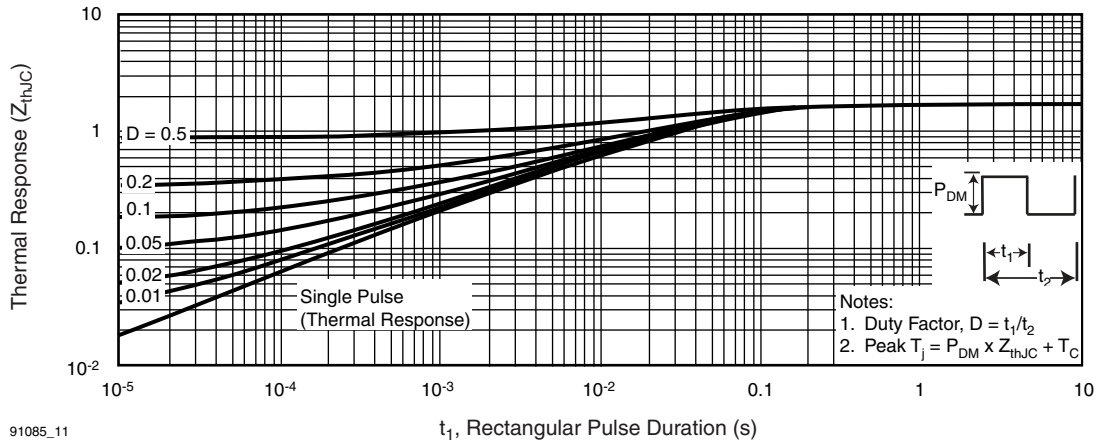


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

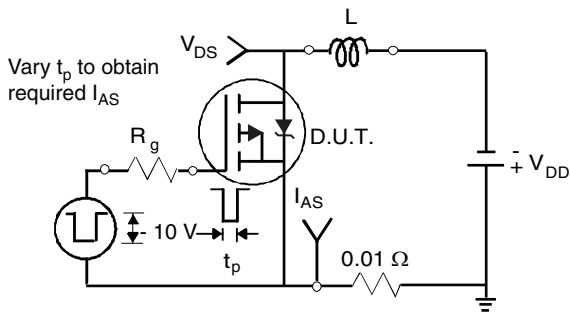


Fig. 12a - Unclamped Inductive Test Circuit

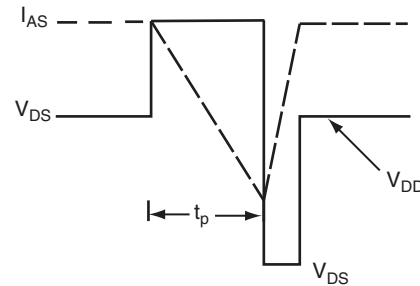


Fig. 12b - Unclamped Inductive Waveforms

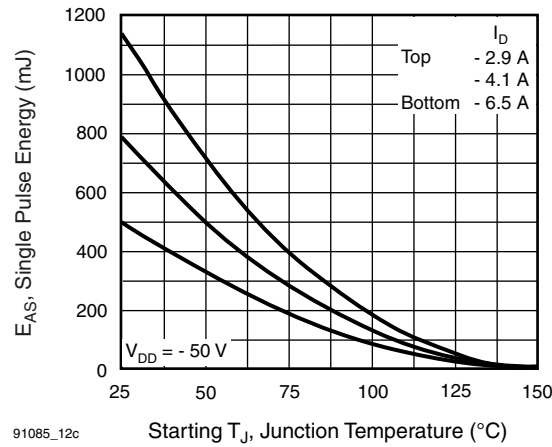


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

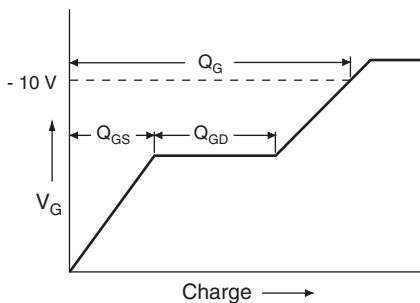


Fig. 13a - Basic Gate Charge Waveform

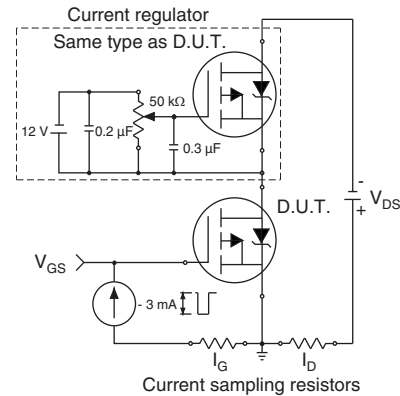
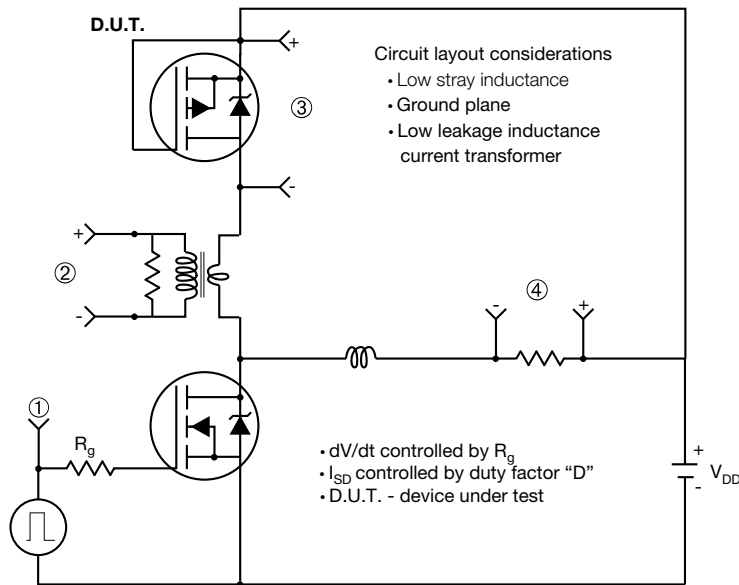
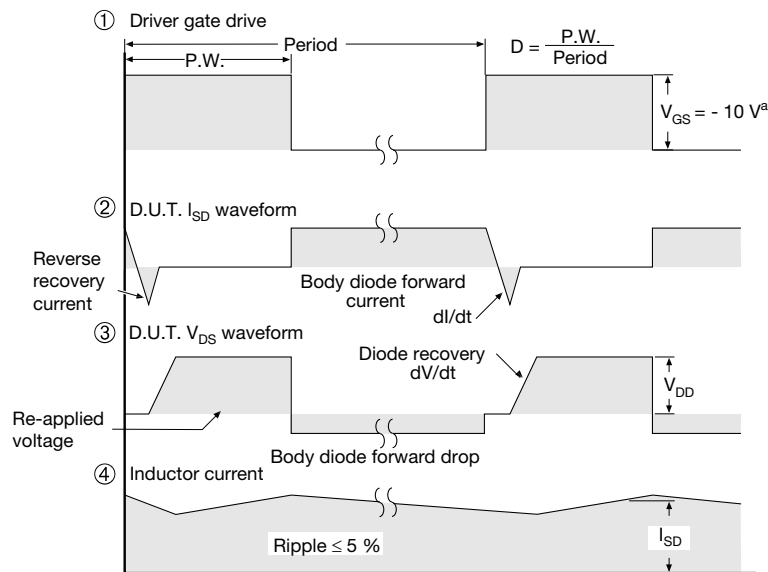


Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



Note
• Compliment N-Channel of D.U.T. for driver



Note
a. $V_{GS} = -5\text{ V}$ for logic level and -3 V drive devices

Fig. 14 - For P-Channel

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?91085.

TO-263AB (HIGH VOLTAGE)



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.06	4.83	0.160	0.190
A1	0.00	0.25	0.000	0.010
b	0.51	0.99	0.020	0.039
b1	0.51	0.89	0.020	0.035
b2	1.14	1.78	0.045	0.070
b3	1.14	1.73	0.045	0.068
c	0.38	0.74	0.015	0.029
c1	0.38	0.58	0.015	0.023
c2	1.14	1.65	0.045	0.065
D	8.38	9.65	0.330	0.380

DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
D1	6.86	-	0.270	-
E	9.65	10.67	0.380	0.420
E1	6.22	-	0.245	-
e	2.54 BSC		0.100 BSC	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	-	1.65	-	0.066
L2	-	1.78	-	0.070
L3	0.25 BSC		0.010 BSC	
L4	4.78	5.28	0.188	0.208

ECN: S-82110-Rev. A, 15-Sep-08
DWG: 5970

Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Dimensions are shown in millimeters (inches).
3. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body at datum A.
4. Thermal PAD contour optional within dimension E, L1, D1 and E1.
5. Dimension b1 and c1 apply to base metal only.
6. Datum A and B to be determined at datum plane H.
7. Outline conforms to JEDEC outline to TO-263AB.



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Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.



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- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

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- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)

Факс: 8 (812) 320-02-42

Электронная почта: org@eplast1.ru

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.